Abstracts

A general parameter-extraction method for transistor noise models

J. Stenarson, M. Garcia, I. Angelov and H. Zirath. "A general parameter-extraction method for transistor noise models." 1999 Transactions on Microwave Theory and Techniques 47.12 (Dec. 1999 [T-MTT] (Special Issue on 1999 International Microwave Symposium)): 2358-2363.

A general direct extraction procedure for transistor noise models that includes two correlated noise sources is developed. Using direct extraction methods instead of optimization make it possible to study the frequency dependence of the model parameters. The extraction procedure is demonstrated for a silicon carbide MESFET, using both PRC and Pospieszalski models. The extracted models show good agreement with measured noise parameters.

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